

ABSTRACT

A plurality of semiconductor layers including a light-emitting layer (14) are formed on the main surface of a substrate (10) which is composed of a group III-V nitride semiconductor. A first n-type semiconductor layer (12) containing indium is formed between the light-emitting layer (14) and the substrate (10), thereby reducing the affect of damage in the substrate surface. By having such a structure, there is realized a semiconductor light-emitting device having uniform characteristics.